

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J352F

# 1. Applications

· Power Management Switches

#### 2. Features

- (1) 1.8 V gate drive voltage.
- (2) Low drain-source on-resistance

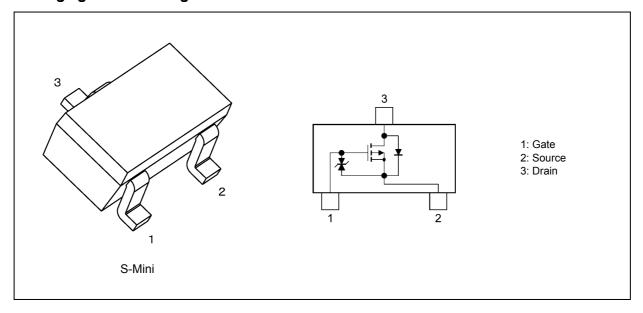
 $: R_{DS(ON)} = 443 \text{ m}\Omega \text{ (max) } (@V_{GS} = -1.8 \text{ V})$ 

 $R_{\rm DS(ON)} = 199 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -2.5 \ {\rm V})$ 

 $R_{\mathrm{DS(ON)}} = 136 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@V_{\mathrm{GS}} = \text{-}4.5 \ \mathrm{V})$ 

 $R_{DS(ON)} = 110 \text{ m}\Omega \text{ (max) } (@V_{GS} = -10 \text{ V})$ 

#### 3. Packaging and Pin Assignment





## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics				Rating	Unit
Drain-source voltage			$V_{DSS}$	-20	V
Gate-source voltage	,		$V_{GSS}$	±12	
Drain current (DC)		(Note 1)	$I_D$	-2	Α
Drain current (pulsed)	,	(Note 1), (Note 2)	$I_{DP}$	-4	
Power dissipation	,	(Note 3)	$P_{D}$	600	mW
Power dissipation	t ≤ 1 s	(Note 3)		1200	
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Repetitive rating; pulse width limited by maximum channel temperature.
- Note 3: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)
- Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

## 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$	_	_	±1	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	_	_	-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 8 V	-12	_	_	
Gate threshold voltage		V <sub>th</sub>	$V_{DS} = -3 \text{ V}, I_{D} = -1 \text{ mA}$	-0.50	_	-1.20	
Drain-source on-resistance	(Note 2)	R <sub>DS(ON)</sub>	$I_D = -0.4 \text{ A}, V_{GS} = -1.8 \text{ V}$	_	210	443	mΩ
			I <sub>D</sub> = -0.6 A, V <sub>GS</sub> = -2.5 V	_	147	199	
			I <sub>D</sub> = -2.0 A, V <sub>GS</sub> = -4.5 V	_	108	136	
			I <sub>D</sub> = -2.0 A, V <sub>GS</sub> = -10 V	_	90	110	
Forward transfer admittance	(Note 2)	Y <sub>fs</sub>	$V_{DS} = -3 \text{ V}, I_{D} = -1 \text{ A}$	_	3.8	_	S

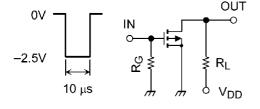
Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Pulse measurement.

## 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V,	_	210	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	31	_	
Output capacitance	C <sub>oss</sub>		_	39	_	
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -1 A,	_	31	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS}$ = 0 to -2.5 V, $R_{G}$ = 10 $\Omega$	_	54	_	

## 5.3. Switching Time Test Circuit



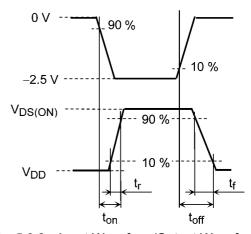


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} = -10 \text{ V}, I_D = -2.0 \text{ A},$		5.1	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	$V_{GS} = -4.5 \text{ V}$		2.3	_	
Gate-drain charge	$Q_{gd}$		_	1.5	_	

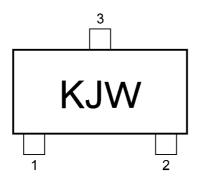


# 5.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

	Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
I	Diode forward voltage	(Note 1)	$V_{DSF}$	I <sub>D</sub> = 2 A, V <sub>GS</sub> = 0 V	_	0.9	1.2	V

Note 1: Pulse measurement.

## 6. Marking



#### 7. Characteristics Curves (Note)

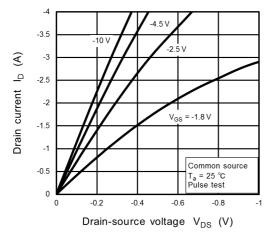


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>

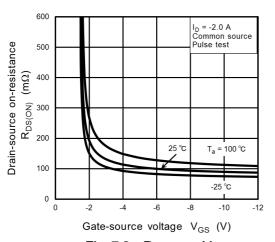


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

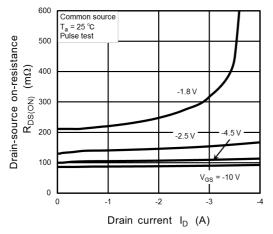


Fig. 7.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

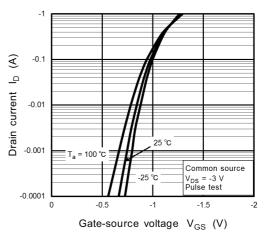


Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

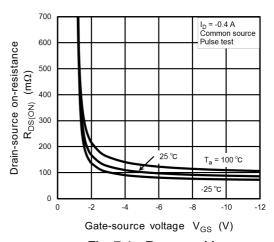


Fig. 7.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

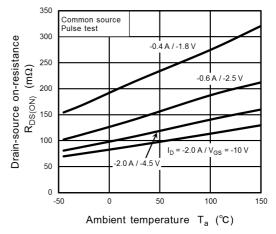
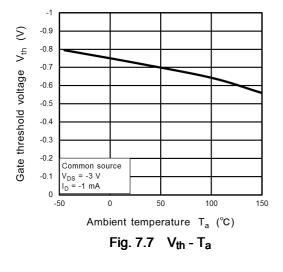


Fig. 7.6  $R_{DS(ON)}$  -  $T_a$ 



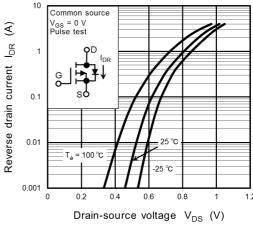
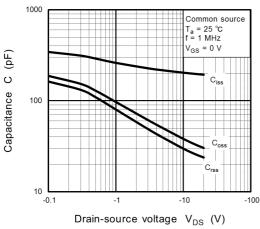


Fig. 7.8 I<sub>DR</sub> - V<sub>DS</sub>



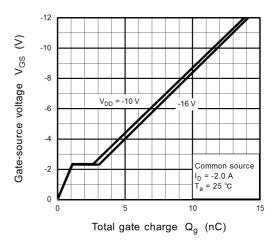
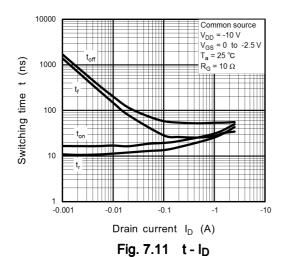


Fig. 7.9 C - V<sub>DS</sub>





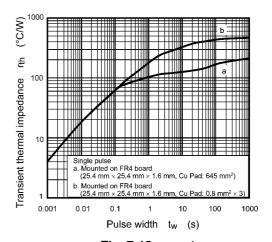


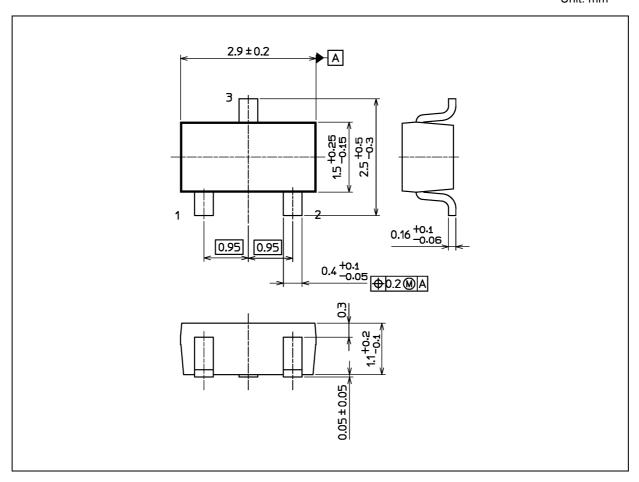
Fig. 7.12 rth - tw

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 12 mg (typ.)

Package Name(s)
TOSHIBA: 2-3F1S
Nickname: S-Mini



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